

A Computational Study of the Electron Transport in HgCdTe Bulk Semiconductor

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Abstract : This paper deals with the use of computational method based on Monte Carlo simulation in order to investigate the transport phenomena of the electron in HgCdTe narrow band gap semiconductor. Via this method we can evaluate the time dependence of the transport parameters: velocity, energy and mobility of electrons through matter (HgCdTe).

Keywords : Monte Carlo, transport parameters, HgCdTe, computational mechanics

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